

## RJL6013DPP

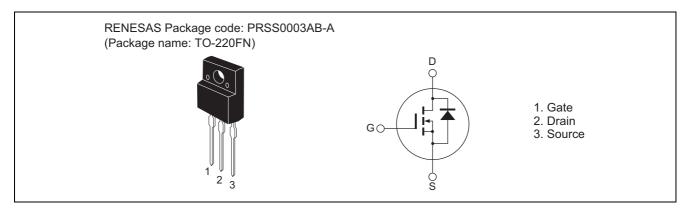
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1691-0200 Rev.2.00 Jun 13, 2008

### **Features**

- Built-in fast recovery diode
- Low on-resistance
- Low leakage current
- High speed switching

### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit	
Drain to source voltage	V <sub>DSS</sub>	600	V	
Gate to source voltage	$V_{GSS}$	±30	V	
Drain current	I <sub>D</sub> Note4	11	А	
Drain peak current	I <sub>D (pulse)</sub> Note1	33	А	
Body-drain diode reverse drain current	I <sub>DR</sub>	11	А	
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub> Note1	33	А	
Avalanche current	I <sub>AP</sub> Note3	4	А	
Avalanche energy	E <sub>AR</sub> Note3	0.87	mJ	
Channel dissipation	Pch Note2	30	W	
Channel to case thermal impedance	θch-c	4.17	°C/W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tc = 25°C
- 3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area

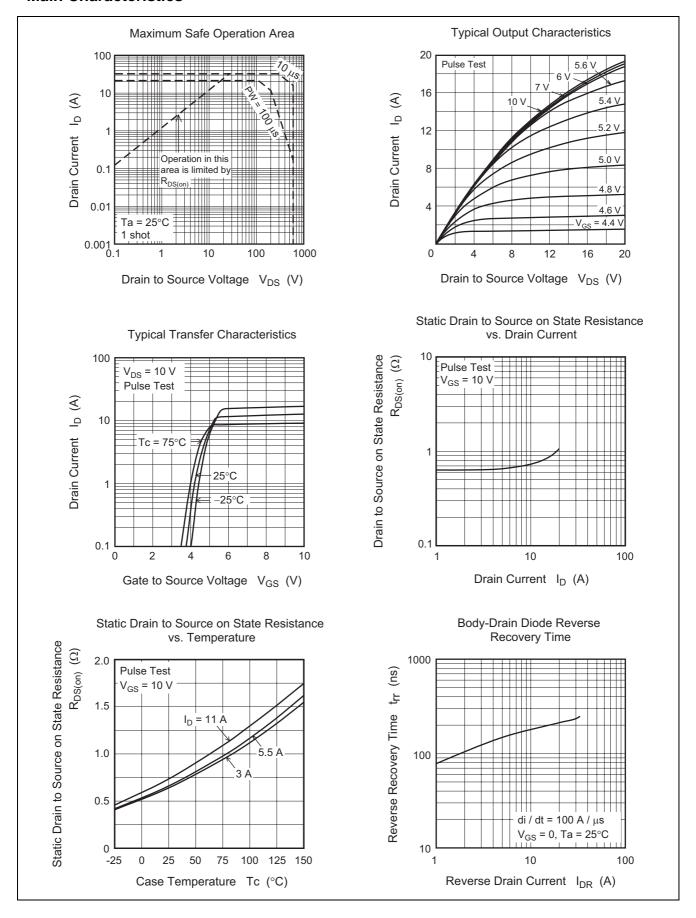
### **Electrical Characteristics**

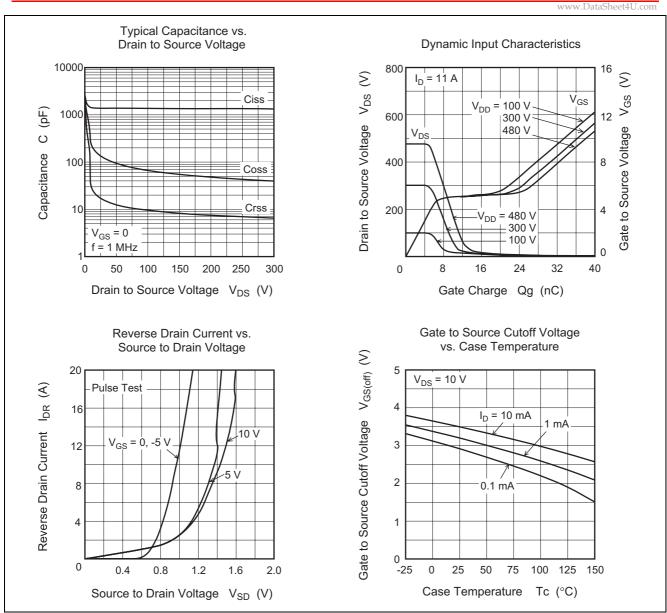
 $(Ta = 25^{\circ}C)$ 

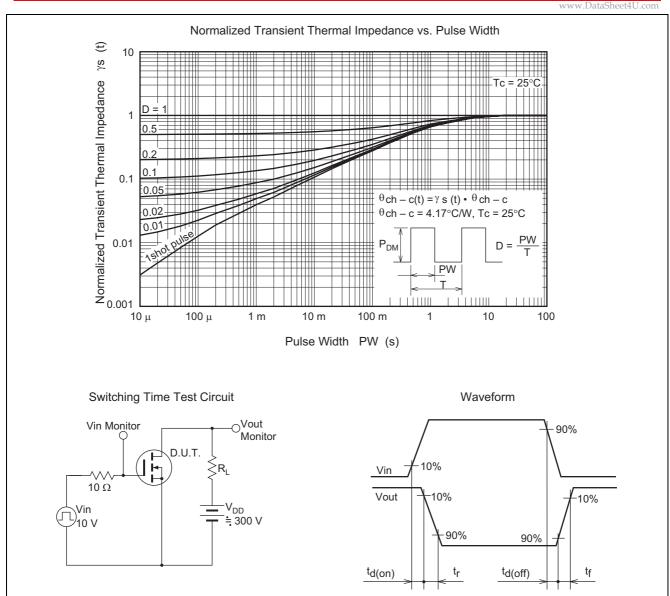
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	10	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	_	4.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>	_	0.66	0.81	Ω	$I_D = 5.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$
Input capacitance	Ciss	_	1400	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	135	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	17	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	_	30	_	ns	$I_D = 5.5 \text{ A}$
Rise time	t <sub>r</sub>	_	20	_	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	$t_{d(off)}$	_	89	_	ns	$R_L = 54.5 \Omega$
Fall time	t <sub>f</sub>	_	16	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	38	_	nC	V <sub>DD</sub> = 480 V
Gate to source charge	Qgs	_	6.6	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	17.2	_	nC	I <sub>D</sub> = 11 A
Body-drain diode forward voltage	$V_{DF}$	_	1.0	1.7	V	$I_F = 11 \text{ A}, V_{GS} = 0^{\text{Note5}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	180	_	ns	$I_F = 11 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 5. Pulse test

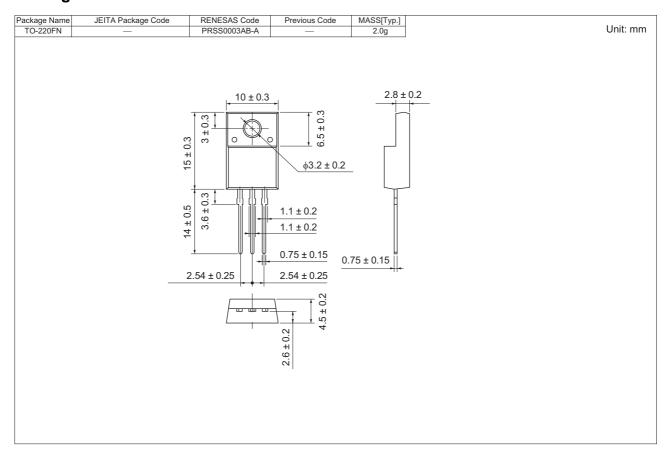
### **Main Characteristics**







### **Package Dimensions**



### **Ordering Information**

Part No.	Quantity	Shipping Container
RJL6013DPP-00-T2	1050 pcs	Box (Tube)

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